Renesas Electronics America Inc - R5F100LFDFB#50 Datasheet

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100lfdfb-50

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	–	–	–	R5F100AG	R5F100BG	R5F100CG
	–		–	–	–	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	–	–	–	R5F100AF	R5F100BF	R5F100CF
	–		–	–	–	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	–		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	–		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	–		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	–		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	–	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	–		–	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	–	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	–		–	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	–	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	–		–	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	–		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	–
	–		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	–
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	–
	–		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	–
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	–	–	–
	–		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	–	–	–
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	–	–	–
	–		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	–	–	–
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	–	–	–
	–		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	–	–	–
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	–	–	–	–	–
	–		R5F101EA	R5F101FA	R5F101GA	–	–	–	–	–

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H
R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H
R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H
R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

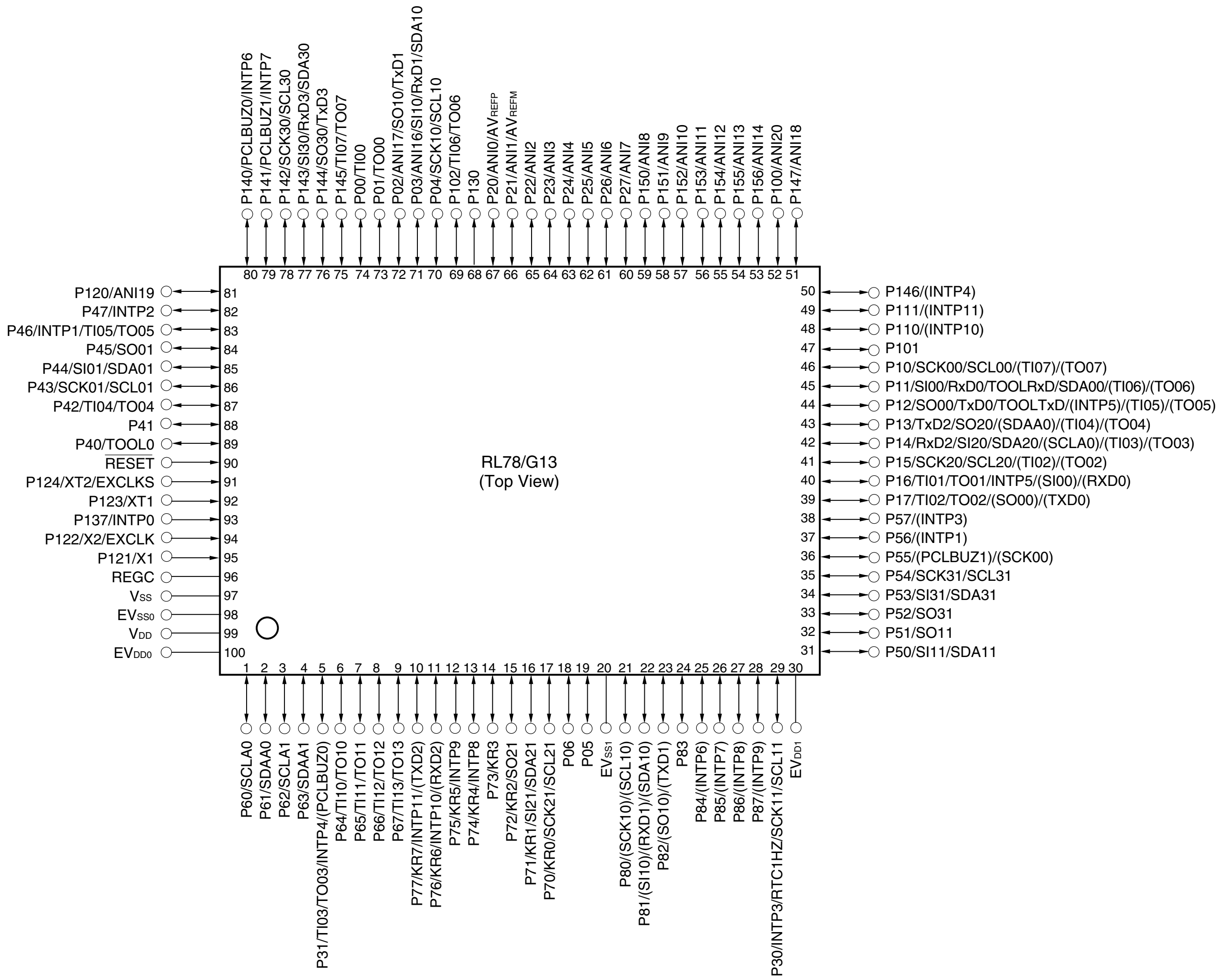
(10/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	A	R5F100MFAFA#V0, R5F100MGAFA#V0, R5F100MHAFA#V0, R5F100MJAFA#V0, R5F100MKAFA#V0, R5F100MLAFA#V0 R5F100MFAFA#X0, R5F100MGAFA#X0, R5F100MHAFA#X0, R5F100MJAFA#X0, R5F100MKAFA#X0, R5F100MLAFA#X0
			D	R5F100MFDFA#V0, R5F100MGDFA#V0, R5F100MHDFA#V0, R5F100MJDFA#V0, R5F100MKDFA#V0, R5F100MLDFA#V0 R5F100MFDFA#X0, R5F100MGDFA#X0, R5F100MHDFA#X0, R5F100MJDFA#X0, R5F100MKDFA#X0, R5F100MLDFA#X0
			G	R5F100MFGFA#V0, R5F100MGGFA#V0, R5F100MHGFA#V0, R5F100MJGFA#V0 R5F100MFGFA#X0, R5F100MGGFA#X0, R5F100MHGFA#X0, R5F100MJGFA#X0
		Not mounted	A	R5F101MFAFA#V0, R5F101MGAFA#V0, R5F101MHAFA#V0, R5F101MJAFA#V0, R5F101MKAFA#V0, R5F101MLAFA#V0 R5F101MFAFA#X0, R5F101MGAFA#X0, R5F101MHAFA#X0, R5F101MJAFA#X0, R5F101MKAFA#X0, R5F101MLAFA#X0
			D	R5F101MFDFA#V0, R5F101MGDFA#V0, R5F101MHDFA#V0, R5F101MJDFA#V0, R5F101MKDFA#V0, R5F101MLDFA#V0 R5F101MFDFA#X0, R5F101MGDFA#X0, R5F101MHDFA#X0, R5F101MJDFA#X0, R5F101MKDFA#X0, R5F101MLDFA#X0
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F100MFAFB#V0, R5F100MGAFB#V0, R5F100MHAFB#V0, R5F100MJAFB#V0, R5F100MKAFB#V0, R5F100MLAFB#V0 R5F100MFAFB#X0, R5F100MGAFB#X0, R5F100MHAFB#X0, R5F100MJAFB#X0, R5F100MKAFB#X0, R5F100MLAFB#X0
			D	R5F100MFDFB#V0, R5F100MGDFB#V0, R5F100MHDFB#V0, R5F100MJDFB#V0, R5F100MKDFB#V0, R5F100MLDFB#V0 R5F100MFDFB#X0, R5F100MGDFB#X0, R5F100MHDFB#X0, R5F100MJDFB#X0, R5F100MKDFB#X0, R5F100MLDFB#X0
			G	R5F100MFGFB#V0, R5F100MGGFB#V0, R5F100MHGFB#V0, R5F100MJGFB#V0 R5F100MFGFB#X0, R5F100MGGFB#X0, R5F100MHGFB#X0, R5F100MJGFB#X0
		Not mounted	A	R5F101MFAFB#V0, R5F101MGAFB#V0, R5F101MHAFB#V0, R5F101MJAFB#V0, R5F101MKAFB#V0, R5F101MLAFB#V0 R5F101MFAFB#X0, R5F101MGAFB#X0, R5F101MHAFB#X0, R5F101MJAFB#X0, R5F101MKAFB#X0, R5F101MLAFB#X0
			D	R5F101MFDFB#V0, R5F101MGDFB#V0, R5F101MHDFB#V0, R5F101MJDFB#V0, R5F101MKDFB#V0, R5F101MLDFB#V0 R5F101MFDFB#X0, R5F101MGDFB#X0, R5F101MHDFB#X0, R5F101MJDFB#X0, R5F101MKDFB#X0, R5F101MLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)



Cautions 1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins ($EV_{DD0} = EV_{DD1}$).

3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.

3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2.4 AC Characteristics

(T_A = –40 to +85°C, $1.6\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	$2.7\ V \le V_{DD} \le 5.5\ V$	0.03125		1	μs
				$2.4\ V \le V_{DD} < 2.7\ V$	0.0625		1	μs
			LS (low-speed main) mode	$1.8\ V \le V_{DD} \le 5.5\ V$	0.125		1	μs
			LV (low-voltage main) mode	$1.6\ V \le V_{DD} \le 5.5\ V$	0.25		1	μs
		Subsystem clock (f_{SUB}) operation		$1.8\ V \le V_{DD} \le 5.5\ V$	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	$2.7\ V \le V_{DD} \le 5.5\ V$	0.03125		1	μs
				$2.4\ V \le V_{DD} < 2.7\ V$	0.0625		1	μs
			LS (low-speed main) mode	$1.8\ V \le V_{DD} \le 5.5\ V$	0.125		1	μs
			LV (low-voltage main) mode	$1.8\ V \le V_{DD} \le 5.5\ V$	0.25		1	μs
External system clock frequency	f_{EX}	$2.7\ V \le V_{DD} \le 5.5\ V$			1.0		20.0	MHz
		$2.4\ V \le V_{DD} < 2.7\ V$			1.0		16.0	MHz
		$1.8\ V \le V_{DD} < 2.4\ V$			1.0		8.0	MHz
		$1.6\ V \le V_{DD} < 1.8\ V$			1.0		4.0	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	$2.7\ V \le V_{DD} \le 5.5\ V$			24			ns
		$2.4\ V \le V_{DD} < 2.7\ V$			30			ns
		$1.8\ V \le V_{DD} < 2.4\ V$			60			ns
		$1.6\ V \le V_{DD} < 1.8\ V$			120			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t_{TIH}, t_{TIL}				$1/f_{MCK}+10$			ns[Note]
TO00 to TO07, TO10 to TO17 output frequency	f_{TO}	HS (high-speed main) mode	$4.0\ V \le EV_{DD0} \le 5.5\ V$				16	MHz
			$2.7\ V \le EV_{DD0} < 4.0\ V$				8	MHz
			$1.8\ V \le EV_{DD0} < 2.7\ V$				4	MHz
			$1.6\ V \le EV_{DD0} < 1.8\ V$				2	MHz
		LS (low-speed main) mode	$1.8\ V \le EV_{DD0} \le 5.5\ V$				4	MHz
			$1.6\ V \le EV_{DD0} < 1.8\ V$				2	MHz
		LV (low-voltage main) mode	$1.6\ V \le EV_{DD0} \le 5.5\ V$				2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	$4.0\ V \le EV_{DD0} \le 5.5\ V$				16	MHz
			$2.7\ V \le EV_{DD0} < 4.0\ V$				8	MHz
			$1.8\ V \le EV_{DD0} < 2.7\ V$				4	MHz
			$1.6\ V \le EV_{DD0} < 1.8\ V$				2	MHz
		LS (low-speed main) mode	$1.8\ V \le EV_{DD0} \le 5.5\ V$				4	MHz
			$1.6\ V \le EV_{DD0} < 1.8\ V$				2	MHz
		LV (low-voltage main) mode	$1.8\ V \le EV_{DD0} \le 5.5\ V$				4	MHz
			$1.6\ V \le EV_{DD0} < 1.8\ V$				2	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0	$1.6\ V \le V_{DD} \le 5.5\ V$		1			μs
		INTP1 to INTP11	$1.6\ V \le EV_{DD0} \le 5.5\ V$		1			μs
Key interrupt input low-level width	t_{KR}	KR0 to KR7	$1.8\ V \le EV_{DD0} \le 5.5\ V$		250			ns
			$1.6\ V \le EV_{DD0} < 1.8\ V$		1			μs
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

(**Note** and **Remark** are listed on the next page.)

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}		—		—		ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V	16 MHz < f_{MCK}	8/f_{MCK}		—		—		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK} and 500		6/f_{MCK} and 500		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		6/f_{MCK} and 750		6/f_{MCK} and 750		6/f_{MCK} and 750		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		6/f_{MCK} and 1500		6/f_{MCK} and 1500		6/f_{MCK} and 1500		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		6/f_{MCK} and 1500		6/f_{MCK} and 1500		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 − 7		t_{KCY2}/2 − 7		t_{KCY2}/2 − 7		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 − 8		t_{KCY2}/2 − 8		t_{KCY2}/2 − 8		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 − 18		t_{KCY2}/2 − 18		t_{KCY2}/2 − 18		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 − 66		t_{KCY2}/2 − 66		t_{KCY2}/2 − 66		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		t_{KCY2}/2 − 66		t_{KCY2}/2 − 66		ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	$t_{KCY2}/2 - 12$		$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	$t_{KCY2}/2 - 18$		$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	$1/f_{MCK} + 20$		$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	$1/f_{MCK} + 20$		$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}		$1/f_{MCK} + 31$		$1/f_{MCK} + 31$		$1/f_{MCK} + 31$		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$2/f_{MCK} + 120$		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$2/f_{MCK} + 214$		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$	ns

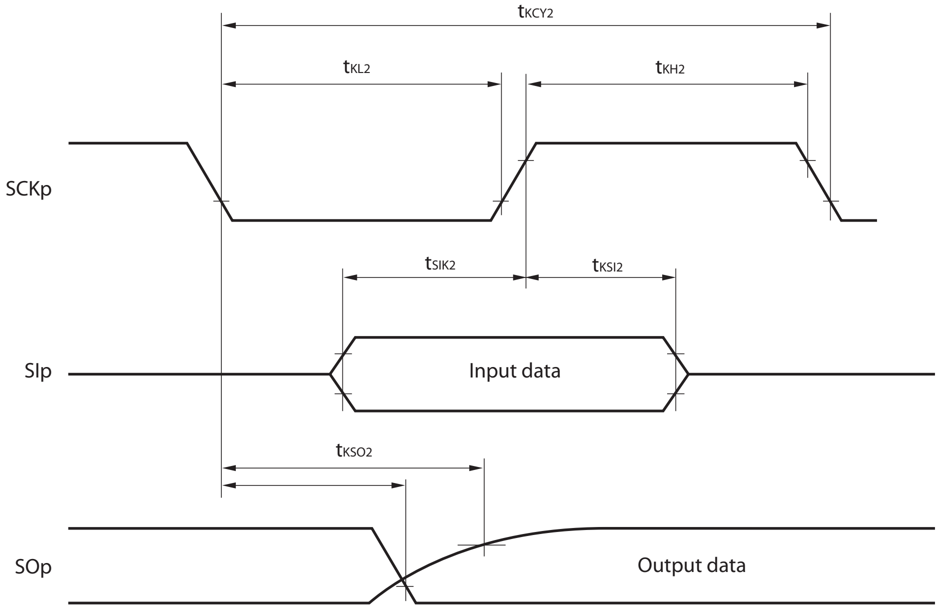
Notes

1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps
2. Use it with EV_{DD0} ≥ V_b.
3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

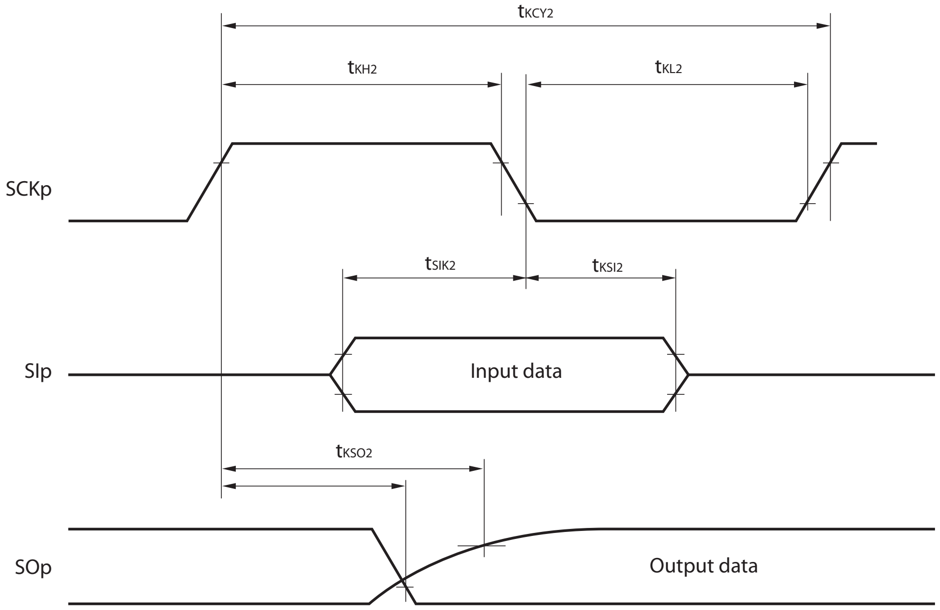
Caution **Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,
n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2.8 Flash Memory Programming Characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	1.8 V ≤ V_{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C	100,000			
		Retained for 20 years T_A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.
The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

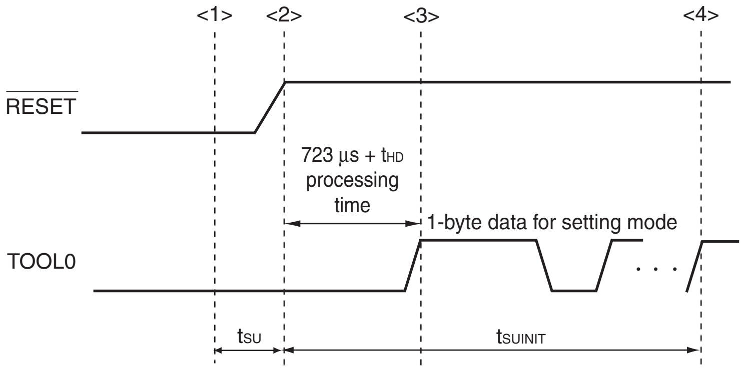
(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

Absolute Maximum Ratings (T_A = 25°C) (2/2)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	−40	mA
		Total of all pins −170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	−70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	−100	mA
	I_{OH2}	Per pin	P20 to P27, P150 to P156	−0.5	mA
		Total of all pins		−2	mA
Output current, low	I_{OL1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	I_{OL2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A	In normal operation mode		−40 to +105	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			−65 to +150	°C

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current [Note 1]	I_{DD1}	Operating mode	HS (high-speed main) mode [Note 5]	f_{IH} = 32 MHz [Note 3]	Basic operation	V_{DD} = 5.0 V		2.1		mA
						V_{DD} = 3.0 V		2.1		mA
					Normal operation	V_{DD} = 5.0 V		4.6	7.5	mA
						V_{DD} = 3.0 V		4.6	7.5	mA
				f_{IH} = 24 MHz [Note 3]	Normal operation	V_{DD} = 5.0 V		3.7	5.8	mA
						V_{DD} = 3.0 V		3.7	5.8	mA
				f_{IH} = 16 MHz [Note 3]	Normal operation	V_{DD} = 5.0 V		2.7	4.2	mA
						V_{DD} = 3.0 V		2.7	4.2	mA
			HS (high-speed main) mode [Note 5]	f_{MX} = 20 MHz [Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		3.0	4.9	mA
						Resonator connection		3.2	5.0	mA
				f_{MX} = 20 MHz [Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		3.0	4.9	mA
						Resonator connection		3.2	5.0	mA
				f_{MX} = 10 MHz [Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		1.9	2.9	mA
						Resonator connection		1.9	2.9	mA
				f_{MX} = 10 MHz [Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		1.9	2.9	mA
						Resonator connection		1.9	2.9	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz [Note 4] T_A = −40°C	Normal operation	Square wave input		4.1	4.9	μA
						Resonator connection		4.2	5.0	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +25°C	Normal operation	Square wave input		4.1	4.9	μA
						Resonator connection		4.2	5.0	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +50°C	Normal operation	Square wave input		4.2	5.5	μA
						Resonator connection		4.3	5.6	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +70°C	Normal operation	Square wave input		4.3	6.3	μA
						Resonator connection		4.4	6.4	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +85°C	Normal operation	Square wave input		4.6	7.7	μA
						Resonator connection		4.7	7.8	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +105°C	Normal operation	Square wave input		6.9	19.7	μA
						Resonator connection		7.0	19.8	μA

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7\ \text{V} \leq V_{DD} \leq 5.5\ \text{V}$@1 MHz to 32 MHz
$2.4\ \text{V} \leq V_{DD} \leq 5.5\ \text{V}$@1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Notes **1.** Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator and subsystem clock are stopped.

4. When high-speed system clock and subsystem clock are stopped.

5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V $\leq V_{DD} \leq$ 5.5 V@1 MHz to 32 MHz
2.4 V $\leq V_{DD} \leq$ 5.5 V@1 MHz to 16 MHz

8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks **1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)
(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V	250		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2 - 24$		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2 - 36$		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2 - 76$		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		66		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		66		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		113		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			50	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when $2.4\ V \le EV_{DD0} < 3.3\ V$ and $1.6\ V \le V_b \le 2.0\ V$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3}\ [\text{bps}]$$

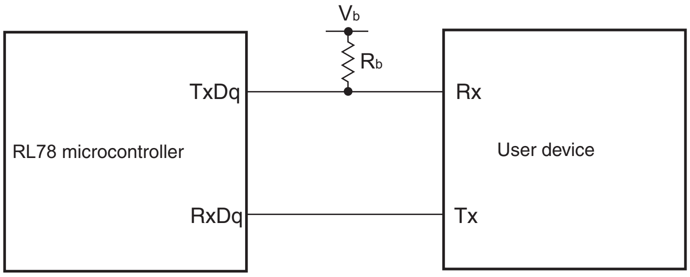
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

($T_A = -40$ to $+105°C$, $2.4 \text{ V} \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time [Note 1]	t_{KCY2}	$4.0 \text{ V} \le EV_{DD0} \le 5.5 \text{ V}$, $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$	$24 \text{ MHz} < f_{MCK}$	$28/f_{MCK}$		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	$24/f_{MCK}$		ns
			$8 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	$20/f_{MCK}$		ns
			$4 \text{ MHz} < f_{MCK} \le 8 \text{ MHz}$	$16/f_{MCK}$		ns
			$f_{MCK} \le 4 \text{ MHz}$	$12/f_{MCK}$		ns
		$2.7 \text{ V} \le EV_{DD0} < 4.0 \text{ V}$, $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$	$24 \text{ MHz} < f_{MCK}$	$40/f_{MCK}$		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	$32/f_{MCK}$		ns
			$16 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	$28/f_{MCK}$		ns
			$8 \text{ MHz} < f_{MCK} \le 16 \text{ MHz}$	$24/f_{MCK}$		ns
			$4 \text{ MHz} < f_{MCK} \le 8 \text{ MHz}$	$16/f_{MCK}$		ns
			$f_{MCK} \le 4 \text{ MHz}$	$12/f_{MCK}$		ns
		$2.4 \text{ V} \le EV_{DD0} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$	$24 \text{ MHz} < f_{MCK}$	$96/f_{MCK}$		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	$72/f_{MCK}$		ns
			$16 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	$64/f_{MCK}$		ns
			$8 \text{ MHz} < f_{MCK} \le 16 \text{ MHz}$	$52/f_{MCK}$		ns
			$4 \text{ MHz} < f_{MCK} \le 8 \text{ MHz}$	$32/f_{MCK}$		ns
			$f_{MCK} \le 4 \text{ MHz}$	$20/f_{MCK}$		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	$4.0 \text{ V} \le EV_{DD0} \le 5.5 \text{ V}$, $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$		$t_{KCY2}/2 - 24$		ns
		$2.7 \text{ V} \le EV_{DD0} < 4.0 \text{ V}$, $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$		$t_{KCY2}/2 - 36$		ns
		$2.4 \text{ V} \le EV_{DD0} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$ [Note 2]		$t_{KCY2}/2 - 100$		ns
SIp setup time (to SCKp↑) [Note2]	t_{SIK2}	$4.0 \text{ V} \le EV_{DD0} \le 5.5 \text{ V}$, $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$		$1/f_{MCK} + 40$		ns
		$2.7 \text{ V} \le EV_{DD0} < 4.0 \text{ V}$, $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$		$1/f_{MCK} + 40$		ns
		$2.4 \text{ V} \le EV_{DD0} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$		$1/f_{MCK} + 60$		ns
SIp hold time (from SCKp↑) [Note 3]	t_{KSI2}			$1/f_{MCK} + 62$		ns
Delay time from SCKp↓ to SOp output [Note 4]	t_{KSO2}	$4.0 \text{ V} \le EV_{DD0} \le 5.5 \text{ V}$, $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 1.4 \text{ k}\Omega$			$2/f_{MCK} + 240$	ns
		$2.7 \text{ V} \le EV_{DD0} < 4.0 \text{ V}$, $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 2.7 \text{ k}\Omega$			$2/f_{MCK} + 428$	ns
		$2.4 \text{ V} \le EV_{DD0} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$ $C_b = 30 \text{ pF}$, $R_b = 5.5 \text{ k}\Omega$			$2/f_{MCK} + 1146$	ns

(**Notes**, **Caution** and **Remarks** are listed on the next page.)

3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = –40 to +105°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD0}	Power supply rise time	3.90	4.06	4.22	V
			Power supply fall time	3.83	3.98	4.13	V
		V_{LVD1}	Power supply rise time	3.60	3.75	3.90	V
			Power supply fall time	3.53	3.67	3.81	V
		V_{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		V_{LVD3}	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V_{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V_{LVD5}	Power supply rise time	2.70	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V_{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V_{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width		t_{LW}		300			µs
Detection delay time						300	µs

LVD Detection Voltage of Interrupt & Reset Mode

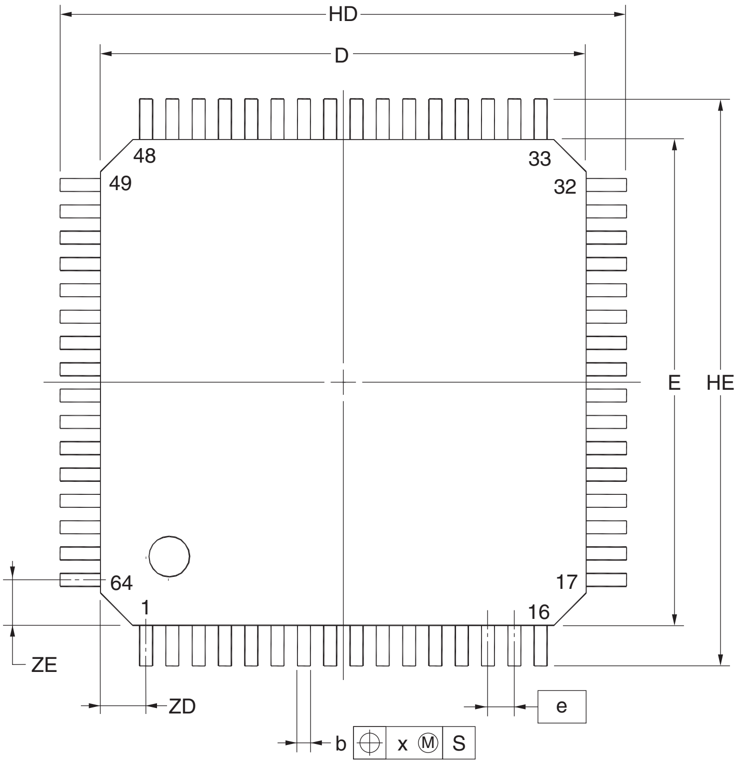
(T_A = –40 to +105°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

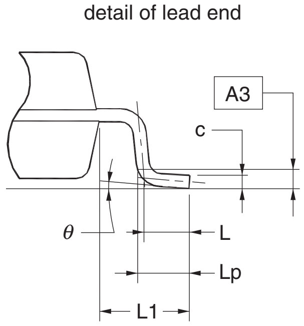
Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 1, falling reset voltage			2.64	2.75	2.86	V
	V_{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	V_{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

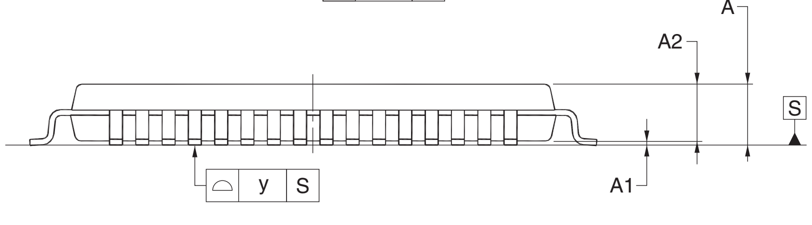
4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA
R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA
R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA
R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA
R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51







(UNIT:mm)

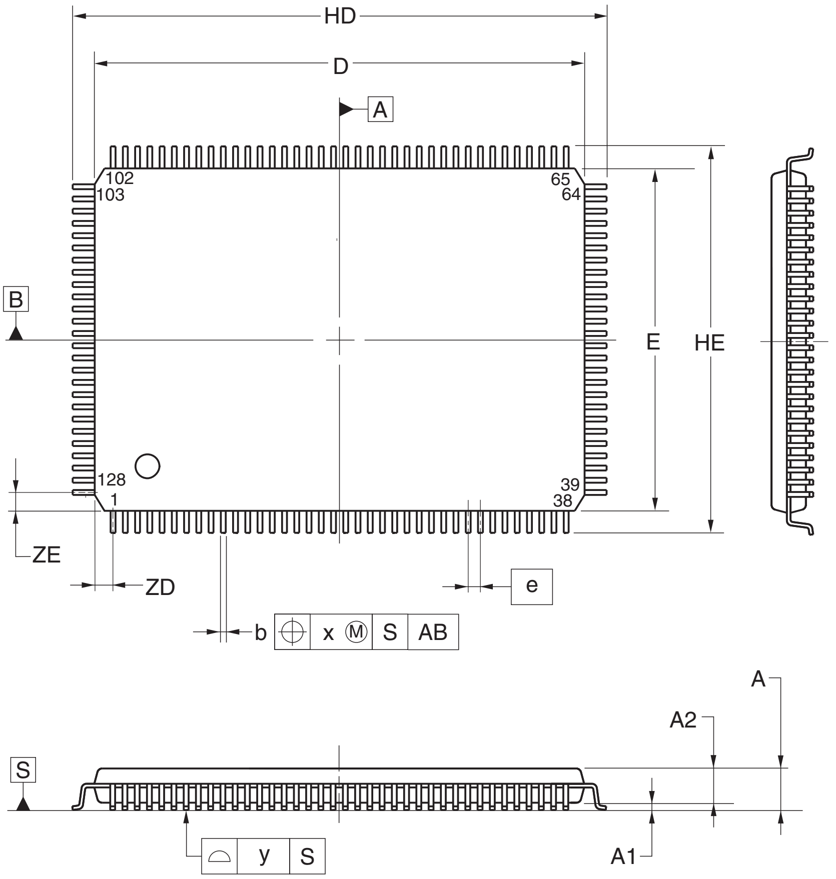
ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^\circ{}^{+5^\circ}_{-3^\circ}$
e	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

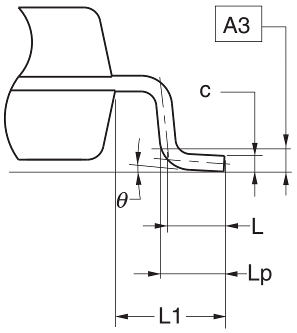
4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB
R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB
R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB
R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3°^{+5°}_{-3°}$
e	0.50
x	0.08
y	0.08
ZD	0.75
ZE	0.75

Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2)
		166	Modification of table in 3.5.2 Serial interface IICA
		166	Modification of IICA serial transfer timing
		167	Addition of table in 3.6.1 A/D converter characteristics
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)
		169	Modification of description in 3.6.1 (2)
		170	Modification of description and note 3 in 3.6.1 (3)
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)
		172	Modification of table and note in 3.6.3 POR circuit characteristics
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes
3.10	Nov 15, 2013	123	Caution 4 added.
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]
			$\overline{\text{ACK}}$ corrected to ACK
			$\overline{\text{ACK}}$ corrected to ACK

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